

ABSTRACT OF THE DISCLOSURE

When a SiC substrate is heated up to around 1800 °C,  
sublimation of SiC occurs from the SiC substrate. Moreover,  
temperature of the front surface of the SiC substrate is lower  
than that of the back surface of the SiC substrate. Therefore,  
sublimation gas sublimed from a back-surface vicinity of the  
substrate, where temperature is high, moves to a front-surface  
vicinity of the substrate, where temperature is low, through the  
hollow micro-pipe defect. Epitaxial growth proceeds on the front  
surface of the substrate while the sublimation gas is  
recrystallized at the front-surface vicinity of the substrate,  
so that the micro-pipe defect is occluded.